

MOS INTEGRATED CIRCUIT μ PD16808

MONOLITHIC DUAL H BRIDGE DRIVER CIRCUIT

DESCRIPTION

The μ PD16808 is a monolithic dual H bridge driver circuit which employing N-channel power MOS FETs for its driver stage. By using the power MOS FETs for the output stage, saturation voltage and power consumption are substantially improved as compared with conventional driver circuits that use bipolar transistors.

Because the dual H bridge driver circuits at the output stage are independent of each other, this IC is ideal as the driver circuit for a 1- to 2-phase excitation bipolar driving stepping motor for the head actuator of an FDD.

FEATURES

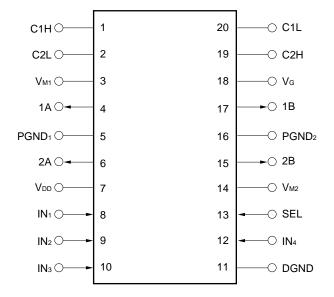
· Low ON resistance (sum of ON resistors of top and bottom FETs)

Ron1 = 1.0 Ω TYP. (VM = 5.0 V) Ron2 = 1.5 Ω TYP. (VM = 12.0 V)

• Low current consumption: IDD = 0.4 mA TYP.

- · Four input modes independently controlling dual H bridge drivers (with 1- to 2-phase excitation selected)
- Motor voltage 12 V/5 V compatible
- Compact surface mount package: 20-pin plastic SOP (300 mil)

PIN CONFIGURATION (Top View)

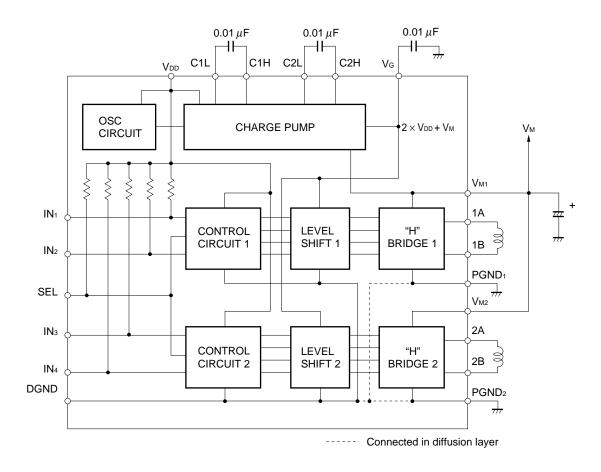




ORDERING INFORMATION

Part Number	Package
μPD16808GS	20-pin plastic SOP (300 mil)

BLOCK DIAGRAM



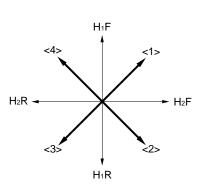
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FUNCTION TABLE

• With 1- to 2-phase excitation selected (SEL = High)

Excitation Direction	IN ₁	IN ₂	INз	IN ₄	H₁	H ₂
	L	L	L	L	S	S
H ₂ R	L	L	L	Н	S	R
H ₂ F	L	L	Н	L	S	F
	L	L	Н	Н	S	S
H ₁ R	L	Н	L	L	R	S
<3>	L	Н	L	Н	R	R
<2>	L	Н	Н	L	R	F
H ₁ R	L	Н	Н	Н	R	S
H₁F	Н	L	L	L	F	S
<4>	Н	L	L	Н	F	R
<1>	Н	L	Н	L	F	F
H₁F	Н	L	Н	Н	F	S
	Н	Н	L	L	S	S
H ₂ R	Н	Н	L	Н	S	R
H ₂ F	Н	Н	Н	L	S	F
	Η	Н	Н	Н	S	S



• With 2-phase excitation selected (SEL = Low)

Excitation Direction	IN ₁	INз	IN ₄	IN ₂	H₁	H ₂
<1>	Н	Н	×	Н	F	F
<2>	L	Н	×	Н	R	F
<3>	L	L	×	Н	R	R
<4>	Н	L	×	Н	F	R
_	×	×	×	L	Stop	

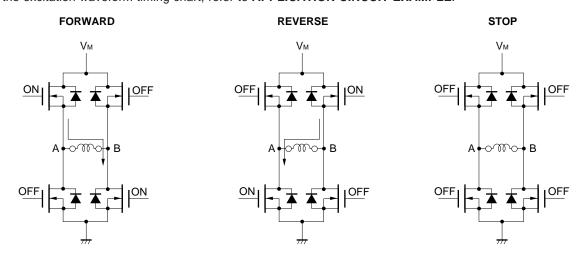
F: Forward

R: Reverse

S: Stop

x: Don't care

For the excitation waveform timing chart, refer to APPLICATION CIRCUIT EXAMPLE.





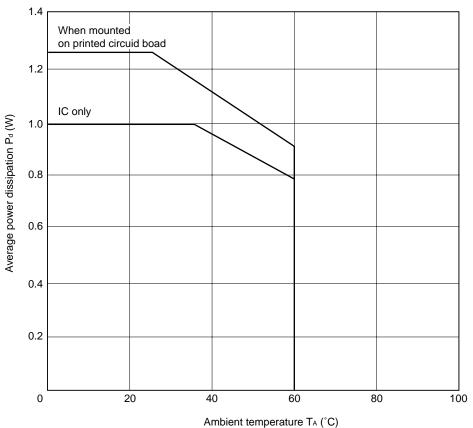
ABSOLUTE MAXIMUM RATINGS (T_A = 25 $^{\circ}$ C)

Parameter	Symbol	Rating	Unit
Supply voltage (motor block)	VM	-0.5 to +15	V
Supply voltage (control block)	V _{DD}	-0.5 to +7	V
Power dissipation	P _{d1}	1.0Note 1	W
	P _{d2}	1.25 ^{Note 2}	
Instantaneous H bridge driver current	l₀ (pulse)	±1.0Note 2, 3	А
Input voltage	Vin	-0.5 to V _{DD} + 0.5	V
Operating temperature range	TA	0 to 60	°C
Operation junction temperature	T _{jMAX} .	150	°C
Storage temperature range	Tstg	-55 to +125	°C

Notes 1. IC only

- 2. When mounted on a printed circuit board ($100 \times 100 \times 1$ mm, glass epoxy)
- **3.** $t \le 5 \text{ ms, Duty} \le 40 \%$







RECOMMENDED OPERATING CONDITIONS

Paramete	Symbol	MIN.	TYP.	MAX.	Unit	
Supply voltage (motor block)		Vм	4.0	5.0	13.2	V
Supply voltage (control block)		V _{DD}	4.0	5.0	6.0	V
H bridge driver currentNote	1-/2-phase excitation	Idr			±600	mA
V _M = 5.0 V 2-phase excitation					±450	
Charge pump capacitance		C ₁ to C ₃	5		20	nF
Operating temperature		TA	0		60	°C

Note When mounted on a printed circuit board $(100 \times 100 \times 1 \text{ mm}, \text{ glass epoxy})$

ELECTRICAL SPECIFICATIONS (Within recommended operating conditions unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
OFF V _M pin current	Ім	V _M = 6.0 V, V _{DD} = 6.0 V ^{Note 1}			1.0	μΑ
		V _M = 13.2 V, V _{DD} = 6.0 V ^{Note 1}			1.0	mA
V _{DD} pin current	IDD	Note 2		0.4	1.0	mA
Control pin high-level input	Іін	TA = 25 °C, VIN = VDD			1.0	μΑ
current		$0 \le T_A \le 60$ °C, $V_{IN} = V_{DD}$			2.0	
Control pin low-level input	lıL	T _A = 25 °C, V _{IN} = 0 V			-0.18	mA
current		0 ≤ T _A ≤ 60 °C, V _{IN} = 0 V			-0.25	
Control pin input pull-up	Rın	T _A = 25 °C	35	50	65	kΩ
resistance		0 ≤ T _A ≤ 60 °C	25		75	
Control pin high-level input voltage	ViH		3.0		V _{DD} + 0.3	V
Control pin low-level input voltage	VIL		-0.3		0.8	V
H bridge circuit ON	Ron1	V _{DD} = 5 V, V _M = 5 V		1.0	2.0	Ω
resistance ^{Note 3}	R _{ON2}	V _{DD} = 5 V, V _M = 12 V		1.5	3.0	Ω
Ron relative accuracy	ΔR on1	Excitation direction <2>, <4>Note 4			±5	%
	ΔR on2	Excitation direction <1>, <3>			±10	
Charge pump circuit (V _G) turn-ON time	Tong	VDD = 5 V, VM = 5 V		0.2	1.0	ms
H bridge circuit turn-ON time	Толн	$C_1 = C_2 = C_3 = 10 \text{ nF}$			5	μs
H bridge circuit turn-OFF time	Тоғғн	R _M = 20 Ω			5	μs

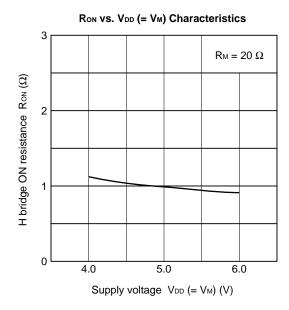
Notes 1. Control pins (IN₁, IN₂, IN₃, IN₄): low

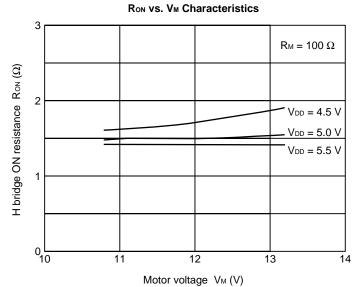
- 2. Control pins (IN1, IN2, IN3, IN4): high
- 3. Sum of ON resistances of top and bottom transistors
- 4. For the excitation direction, refer to **FUNCTION TABLE**.

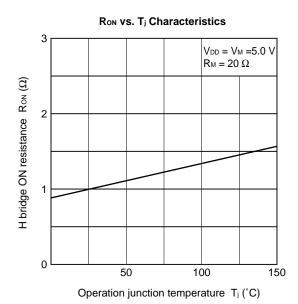
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CHARACTERISTIC CURVES

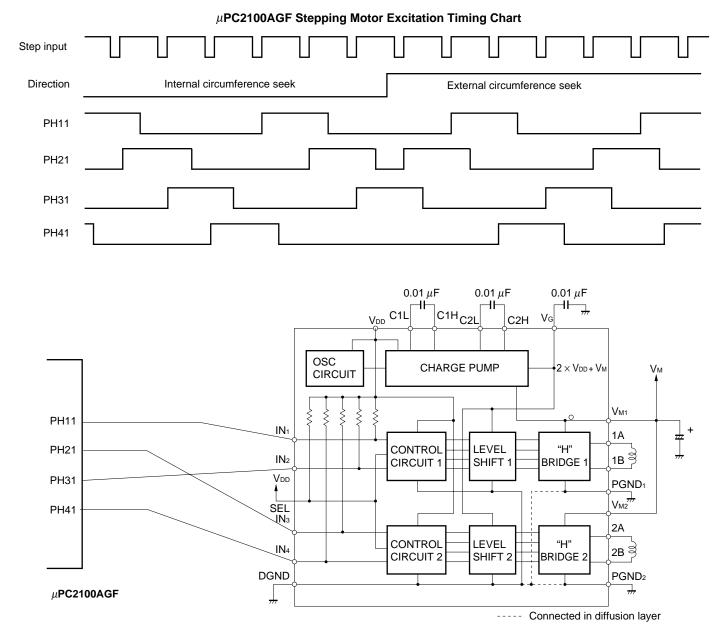


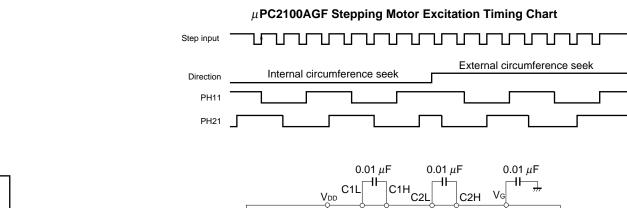


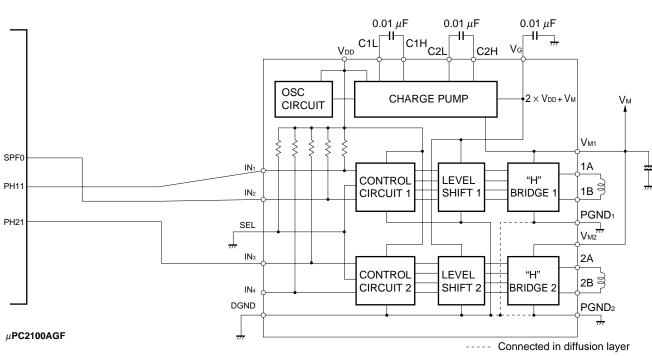


APPLICATION CIRCUIT EXAMPLE

Connection with 1-chip FDD LSI μ PC2100AGF (With 1- to 2-phase excitation selected)

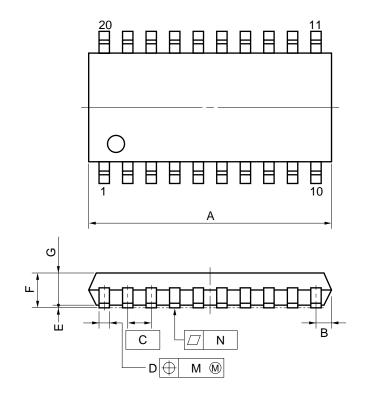




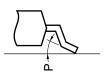


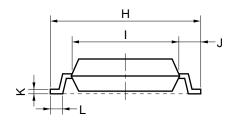
The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

20 PIN PLASTIC SOP (300 mil)



detail of lead end





NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

E 0.1±0.1 0.004±0.004 F 1.8 MAX. 0.071 MAX. G 1.55 0.061 H 7.7±0.3 0.303±0.012 I 5.6 0.220 J 1.1 0.043 K 0.20+0.10 0.008+0.004 K 0.20+0.10 0.008+0.004			
B 0.78 MAX. 0.031 MAX. C 1.27 (T.P.) 0.050 (T.P.) D 0.40+0.10 0.016+0.004 F 1.8 MAX. 0.071 MAX. G 1.55 0.061 H 7.7±0.3 0.303±0.012 I 5.6 0.220 J 1.1 0.043 K 0.20+0.10 0.008+0.004 L 0.6±0.2 0.024+0.008 M 0.12 0.005 N 0.10 0.004	ITEM	MILLIMETERS	INCHES
C 1.27 (T.P.) 0.050 (T.P.) D 0.40 ^{+0.10} _{-0.05} 0.016 ^{+0.004} _{-0.003} E 0.1±0.1 0.004±0.004 F 1.8 MAX. 0.071 MAX. G 1.55 0.061 H 7.7±0.3 0.303±0.012 I 5.6 0.220 J 1.1 0.043 K 0.20 ^{+0.10} _{-0.005} 0.008 ^{+0.004} _{-0.002} L 0.6±0.2 0.024 ^{+0.008} _{-0.009} M 0.12 0.005 N 0.10 0.004	Α	13.00 MAX.	0.512 MAX.
D 0.40 ^{+0.10} _{-0.05} 0.016 ^{+0.004} _{-0.003} E 0.1±0.1 0.004±0.004 F 1.8 MAX. 0.071 MAX. G 1.55 0.061 H 7.7±0.3 0.303±0.012 I 5.6 0.220 J 1.1 0.043 K 0.20 ^{+0.10} _{-0.05} 0.008 ^{+0.004} _{-0.002} L 0.6±0.2 0.024 ^{+0.008} _{-0.009} M 0.12 0.005 N 0.10 0.004	В	0.78 MAX.	0.031 MAX.
E 0.1±0.1 0.004±0.004 F 1.8 MAX. 0.071 MAX. G 1.55 0.061 H 7.7±0.3 0.303±0.012 I 5.6 0.220 J 1.1 0.043 K 0.20+0.10 0.008+0.004 L 0.6±0.2 0.024+0.008 M 0.12 0.005 N 0.10 0.004	С	1.27 (T.P.)	0.050 (T.P.)
F 1.8 MAX. 0.071 MAX. G 1.55 0.061 H 7.7±0.3 0.303±0.012 I 5.6 0.220 J 1.1 0.043 K 0.20+0.10 0.008+0.004 L 0.6±0.2 0.024+0.008 M 0.12 0.005 N 0.10 0.004	D	$0.40^{+0.10}_{-0.05}$	$0.016^{+0.004}_{-0.003}$
G 1.55 0.061 H 7.7±0.3 0.303±0.012 I 5.6 0.220 J 1.1 0.043 K 0.20 ^{+0.10} _{-0.05} 0.008 ^{+0.004} _{-0.002} L 0.6±0.2 0.024 ^{+0.008} _{-0.009} M 0.12 0.005 N 0.10 0.004	Е	0.1±0.1	0.004±0.004
H 7.7±0.3 0.303±0.012 I 5.6 0.220 J 1.1 0.043 K 0.20 ^{+0.10} _{-0.005} 0.008 ^{+0.004} _{-0.002} L 0.6±0.2 0.024 ^{+0.008} _{-0.009} M 0.12 0.005 N 0.10 0.004	F	1.8 MAX.	0.071 MAX.
I 5.6 0.220 J 1.1 0.043 K 0.20 ^{+0.10} _{-0.05} 0.008 ^{+0.004} _{-0.002} L 0.6±0.2 0.024 ^{+0.008} _{-0.009} M 0.12 0.005 N 0.10 0.004	G	1.55	0.061
J 1.1 0.043 K 0.20 ^{+0.10} _{-0.05} 0.008 ^{+0.004} _{-0.002} L 0.6±0.2 0.024 ^{+0.008} _{-0.009} M 0.12 0.005 N 0.10 0.004	Н	7.7±0.3	0.303±0.012
K 0.20 ⁺ 0.10 ₋ 0.05 0.008 ⁺ 0.004 ₋ 0.002 L 0.6±0.2 0.024 ⁺ 0.008 ₋ 0.009 M 0.12 0.005 N 0.10 0.004	1	5.6	0.220
L 0.6±0.2 0.024 ^{+0.008} M 0.12 0.005 N 0.10 0.004	J	1.1	0.043
M 0.12 0.005 N 0.10 0.004	K	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$
N 0.10 0.004	L	0.6±0.2	$0.024^{+0.008}_{-0.009}$
	М	0.12	0.005
P 3°+7° 3°+7°	N	0.10	0.004
	P	3°+7°	3°+7°

P20GM-50-300B, C-4



RECOMMENDED SOLDERING CONDITIONS

It is recommended to solder this product under the conditions described below.

For soldering methods and conditions other than those listed below, consult NEC.

Surface mount type

For the details of the recommended soldering conditions of this type, refer to **Semiconductor Device Mounting Technology Manual (C10535E)**.

Soldering Method	Soldering Conditions	Symbol of Recommended Soldering
Infrared reflow	Peak package temperature: 230 °C, Time: 30 seconds MAX. (210 °C MIN.), Number of times: 1, Number of days: None ^{Note}	IR30-00
VPS	Peak package temperature: 215 °C, Time: 40 seconds MAX. (200 °C MIN.), Number of times: 1, Number of days: None ^{Note}	VP15-00
Wave soldering	Solder bath temperature: 260 °C MAX., Time: 10 seconds MAX., Number of times: 1, Number of days: None ^{Note}	WS60-00
Partial heating	Pin temperature: 300 °C MAX., Time: 10 seconds MAX., Number of days: None ^{Note}	-

Note The number of storage days at 25 °C, 65 % RH after the dry pack has been opened

Caution Do not use two or more soldering methods in combination (except partial heating).

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[MEMO]

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